

LM113/LM313 Reference Diode

General Description

The LM113/LM313 are temperature compensated, low voltage reference diodes. They feature extremely-tight regulation over a wide range of operating currents in addition to an unusually-low breakdown voltage and good temperature stability.

The diodes are synthesized using transistors and resistors in a monolithic integrated circuit. As such, they have the same low noise and long term stability as modern IC op amps. Further, output voltage of the reference depends only on highly-predictable properties of components in the IC; so they can be manufactured and supplied to tight tolerances.

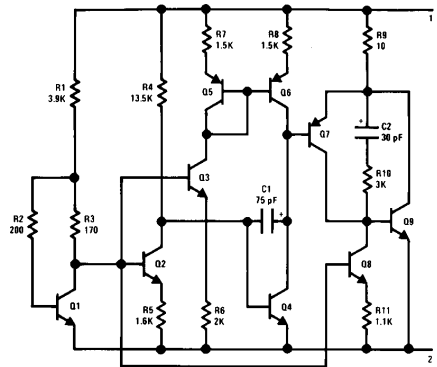
- Dynamic impedance of 0.3Ω from $500\ \mu\text{A}$ to $20\ \text{mA}$
- Temperature stability typically 1% over -55°C to 125°C range (LM113), 0°C to 70°C (LM313)
- Tight tolerance: $\pm 5\%$, $\pm 2\%$ or $\pm 1\%$

The characteristics of this reference recommend it for use in bias-regulation circuitry, in low-voltage power supplies or in battery powered equipment. The fact that the breakdown voltage is equal to a physical property of silicon—the energy-band gap voltage—makes it useful for many temperature-compensation and temperature-measurement functions.

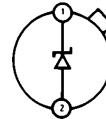
Features

- Low breakdown voltage: 1.220V

Schematic and Connection Diagrams



Metal Can Package



Note: Pin 2 connected to case.
TOP VIEW

Order Number

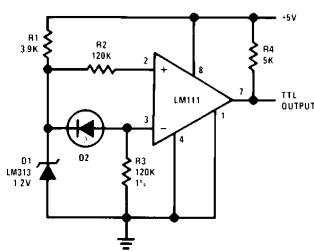
LM113H, LM113H/883,
LM113-1H, LM113-1H/883,
LM113-2H, LM113-2H/883,
or LM313H

See NS Package Number H02A

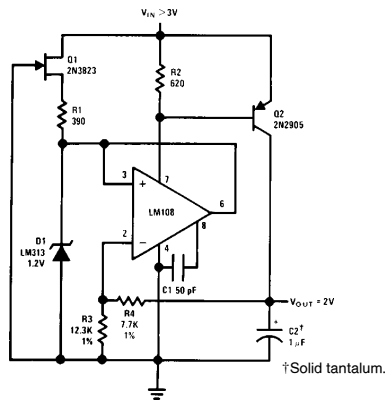
TL/H/5713-1

Typical Applications

Level Detector for Photodiode



Low Voltage Regulator



†Solid tantalum.

TL/H/5713-2

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. (Note 3)

Power Dissipation (Note 1)	100 mW
Reverse Current	50 mA
Forward Current	50 mA

Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C
Operating Temperature Range LM113	-55°C to +125°C
LM313	0°C to +70°C

Electrical Characteristics (Note 2)

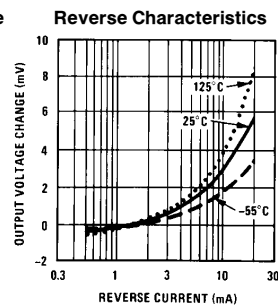
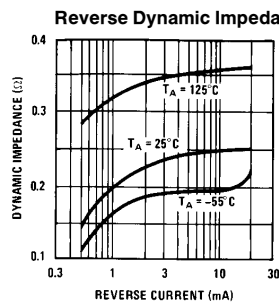
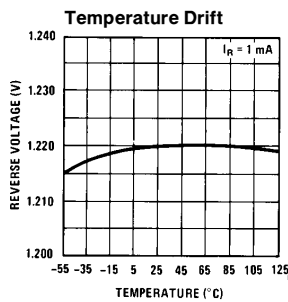
Parameter	Conditions	Min	Typ	Max	Units
Reverse Breakdown Voltage LM113/LM313 LM113-1 LM113-2	$I_R = 1 \text{ mA}$	1.160	1.220	1.280	V
		1.210	1.22	1.232	V
		1.195	1.22	1.245	V
Reverse Breakdown Voltage Change	$0.5 \text{ mA} \leq I_R \leq 20 \text{ mA}$		6.0	15	mV
Reverse Dynamic Impedance	$I_R = 1 \text{ mA}$ $I_R = 10 \text{ mA}$		0.2	1.0	Ω
			0.25	0.8	Ω
Forward Voltage Drop	$I_F = 1.0 \text{ mA}$		0.67	1.0	V
RMS Noise Voltage	$10 \text{ Hz} \leq f \leq 10 \text{ kHz}$ $I_R = 1 \text{ mA}$		5		μV
Reverse Breakdown Voltage Change with Current	$0.5 \text{ mA} \leq I_R \leq 10 \text{ mA}$ $T_{\text{MIN}} \leq T_A \leq T_{\text{MAX}}$			15	mV
Breakdown Voltage Temperature Coefficient	$1.0 \text{ mA} \leq I_R \leq 10 \text{ mA}$ $T_{\text{MIN}} \leq T_A \leq T_{\text{MAX}}$		0.01		%/°C

Note 1: For operating at elevated temperatures, the device must be derated based on a 150°C maximum junction and a thermal resistance of 80°C/W junction to case or 440°C/W junction to ambient.

Note 2: These specifications apply for $T_A = 25^\circ\text{C}$, unless stated otherwise. At high currents, breakdown voltage should be measured with lead lengths less than 1/4 inch. Kelvin contact sockets are also recommended. The diode should not be operated with shunt capacitances between 200 pF and 0.1 μF , unless isolated by at least a 100 Ω resistor, as it may oscillate at some currents.

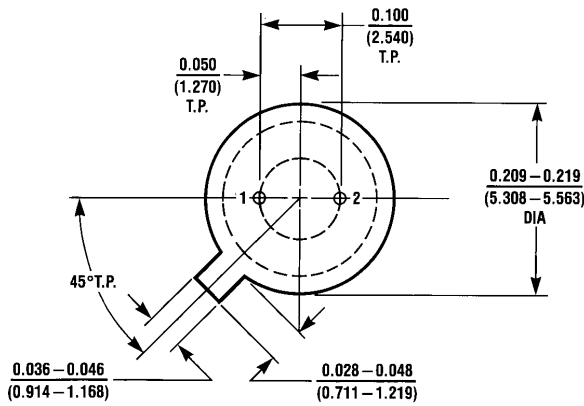
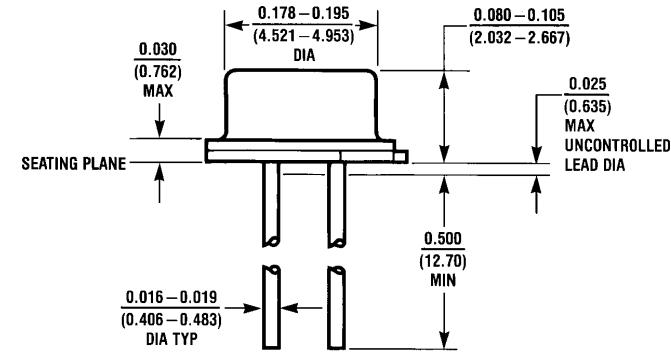
Note 3: Refer to the following RETS drawings for military specifications: RETS113-1X for LM113-1, RETS113-2X for LM113-2 or RETS113X for LM113.

Typical Performance Characteristics



TL/H/5713-3

Physical Dimensions inches (millimeters)



H02A (REV C)

Order Number LM113H, LM113H/883, LM113-1H, LM113-1H/883,
LM113-2H, LM113-2H/883 or LM313H
NS Package Number H02A

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.